

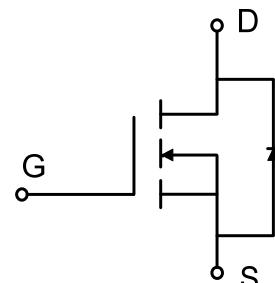
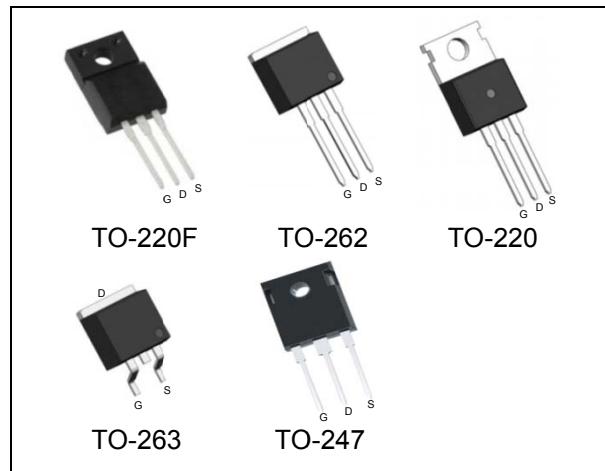
## 650V 0.15Ω Super Junction Power MOSFET

**Description**

WMOS™ F2 is Wayon's 2nd generation super junction MOSFET family with fast body diode. F2 series provide all benefits of a fast switching SJ-MOSFET while offering an extremely fast body diode. WMOS™ F2 makes especially resonant switching applications more reliable.

**Features**

- $V_{DS} = 700V @ T_{j,max}$
- Typ.  $R_{DS(on)} = 0.15\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

**Applications**

LED Lighting, Charger, Adapter, PC, LCD TV, Server

**Absolute Maximum Ratings**

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Drain-source voltage	$V_{DSS}$	650		V
Continuous drain current <sup>1)</sup> $(T_C = 25^\circ C)$	$I_D$	23		A
$(T_C = 100^\circ C)$		13		A
Pulsed drain current <sup>2)</sup>	$I_{DM}$	65		A
Gate-source voltage	$V_{GS}$	$\pm 30$		V
Avalanche energy, single pulse <sup>3)</sup>	$E_{AS}$	210		mJ
Avalanche energy, repetitive <sup>2)</sup>	$E_{AR}$	0.3		mJ
Avalanche current, repetitive <sup>2)</sup>	$I_{AR}$	2.5		A
Power dissipation ( $T_C = 25^\circ C$ ) - Derate above 25°C	$P_D$	160 1.28	31 0.25	W W/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150		°C
Continuous diode forward current	$I_S$	23		A
Diode pulse current	$I_{S,pulse}$	65		A

**Thermal Characteristics**

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.9	4	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	°C/W

**Electrical Characteristics**  $T_c = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0 \text{ V}, I_{\text{D}}=0.25 \text{ mA}$	650	-	-	V
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=0.25 \text{ mA}$	2.5	3.5	4.5	V
Drain cut-off current	$I_{\text{DSS}}$	$V_{\text{DS}}=650 \text{ V}, V_{\text{GS}}=0 \text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	20	$\mu\text{A}$
Gate leakage current, forward	$I_{\text{GSSF}}$	$V_{\text{GS}}=20 \text{ V}, V_{\text{DS}}=0 \text{ V}$	-	-	100	nA
Gate leakage current, reverse	$I_{\text{GSSR}}$	$V_{\text{GS}}=-20 \text{ V}, V_{\text{DS}}=0 \text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=4 \text{ A}$ $T_j = 25^\circ\text{C}$	-	0.15	0.19	$\Omega$
<b>Dynamic characteristics</b>						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=100 \text{ V}, V_{\text{GS}}=0 \text{ V},$ $f = 1 \text{ MHz}$	-	1775	-	pF
Output capacitance	$C_{\text{oss}}$		-	64	-	
Reverse transfer capacitance	$C_{\text{rss}}$		-	1.8	-	
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=300 \text{ V}, I_{\text{D}}=15 \text{ A}$ $R_G = 25 \Omega, V_{\text{GS}}=10 \text{ V}$	-	47	-	ns
Rise time	$t_r$		-	48	-	
Turn-off delay time	$t_{\text{d}(\text{off})}$		-	106	-	
Fall time	$t_f$		-	26	-	
<b>Gate charge characteristics</b>						
Gate to source charge	$Q_{\text{gs}}$	$V_{\text{DD}}=480 \text{ V}, I_{\text{D}}=15 \text{ A},$ $V_{\text{GS}}=0 \text{ to } 10 \text{ V}$	-	9.7	-	nC
Gate to drain charge	$Q_{\text{gd}}$		-	7.3	-	
Gate charge total	$Q_g$		-	27.3	-	
Gate plateau voltage	$V_{\text{plateau}}$		-	5.6	-	V
<b>Reverse diode characteristics</b>						
Diode forward voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0 \text{ V}, I_{\text{F}}=4 \text{ A}$	-	-	1.2	V
Reverse recovery time	$t_{\text{rr}}$	$V_R=50 \text{ V}, I_{\text{F}}=15 \text{ A},$ $dI_{\text{F}}/dt=100 \text{ A}/\mu\text{s}$	-	170	-	ns
Reverse recovery charge	$Q_{\text{rr}}$		-	2.1	-	$\mu\text{C}$
Peak reverse recovery current	$I_{\text{rrm}}$		-	18.8	-	A

Notes:

1. Limited by  $T_{j\max}$ . Maximum duty cycle D=0.5.
2. Repetitive rating: pulse width limited by maximum junction temperature.
3.  $I_{AS} = 2.5 \text{ A}, V_{DD} = 50 \text{ V}, R_G = 25 \Omega$ , starting  $T_j = 25^\circ\text{C}$ .

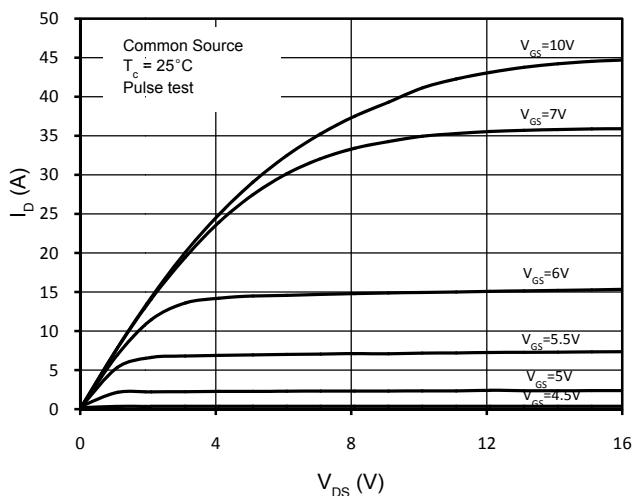


Figure 1. On-Region Characteristics

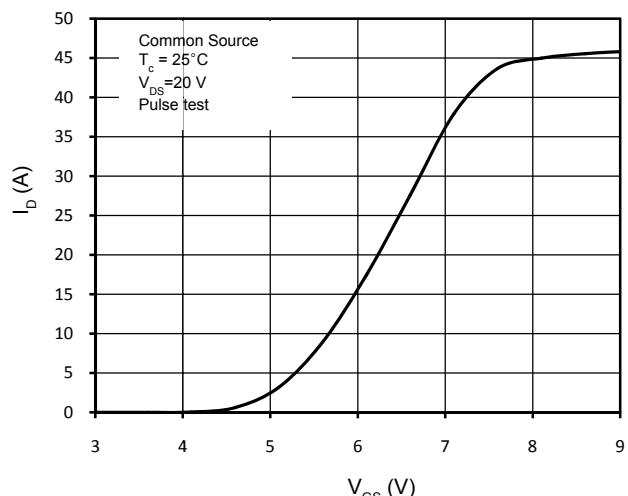


Figure 2. Transfer Characteristics

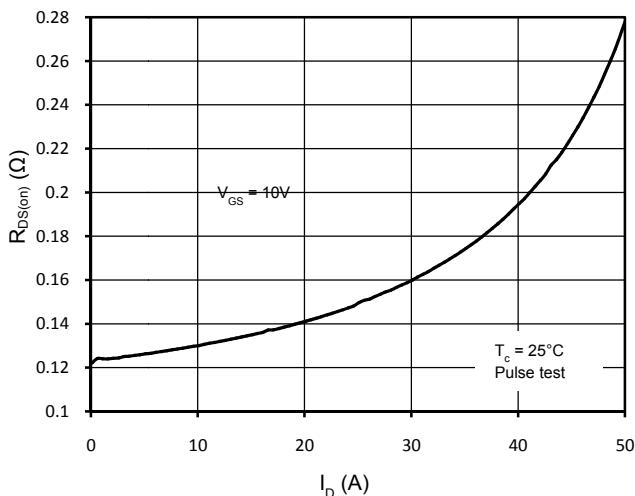


Figure 3. Static Drain-Source On Resistance

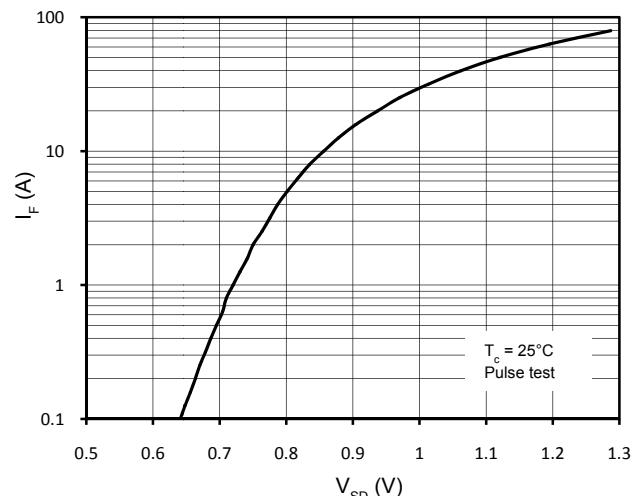
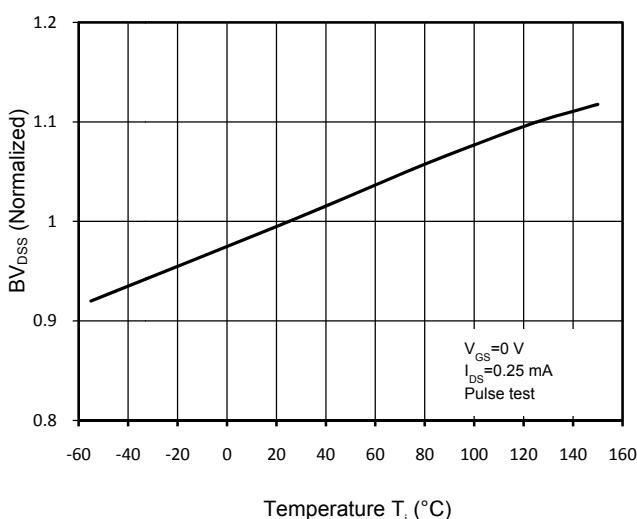
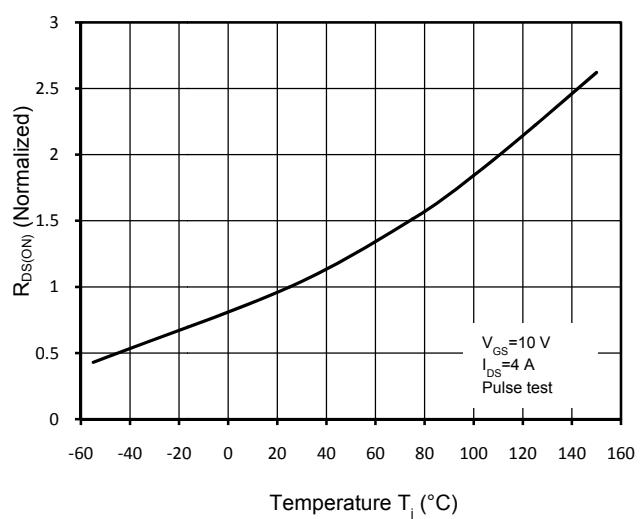


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized  $BV_{DSs}$  vs. TemperatureFigure 6. Normalized  $R_{DS(on)}$  vs. Temperature

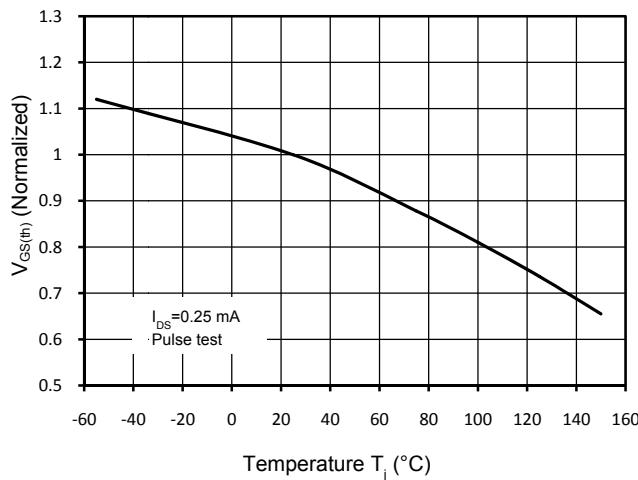


Figure 7. Threshold Voltage vs. Temperature

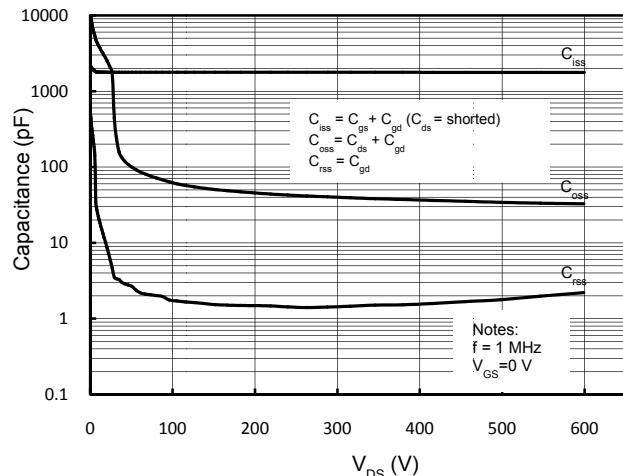


Figure 8. Capacitance Characteristics

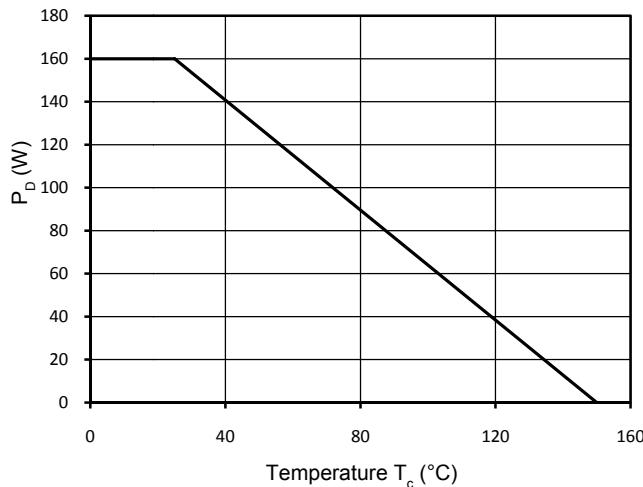


Figure 9. Power Dissipation

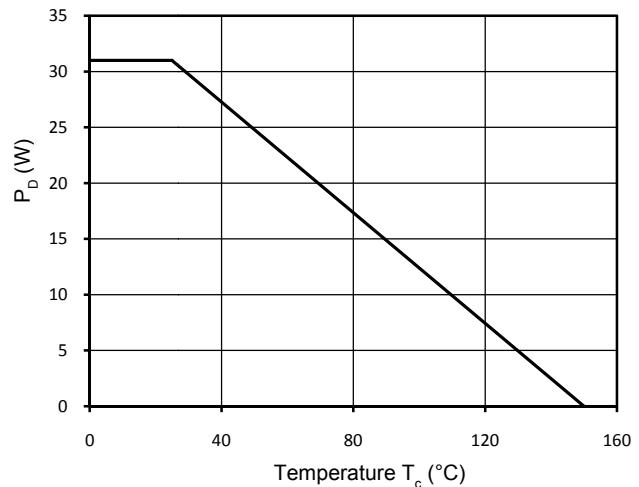


Figure 10. Power Dissipation (TO-220F)

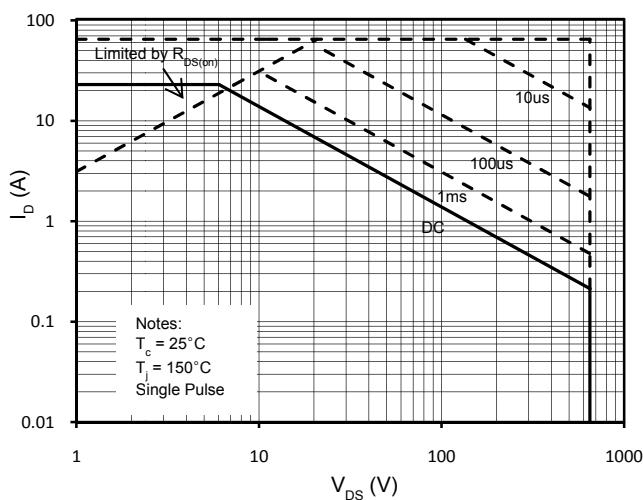


Figure 11. Maximum Safe Operating Area

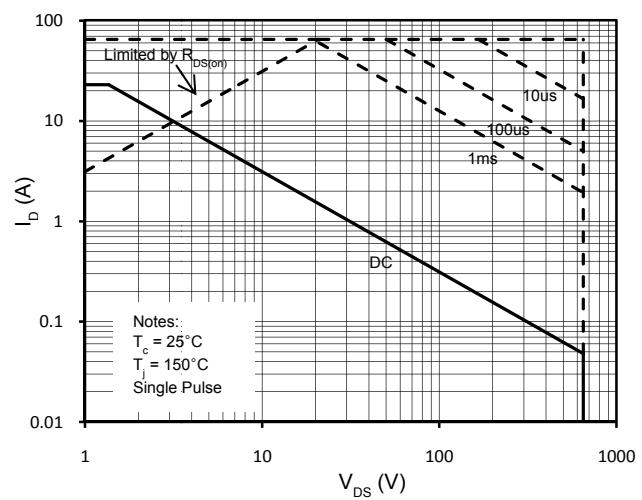


Figure 12. Maximum Safe Operating Area(TO-220F)

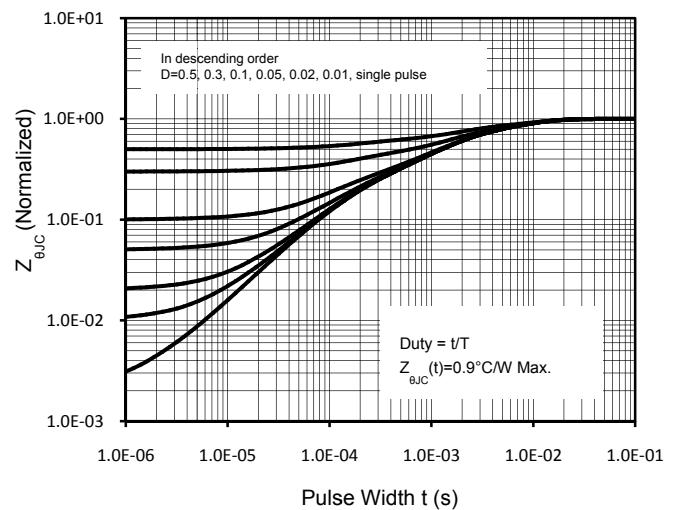
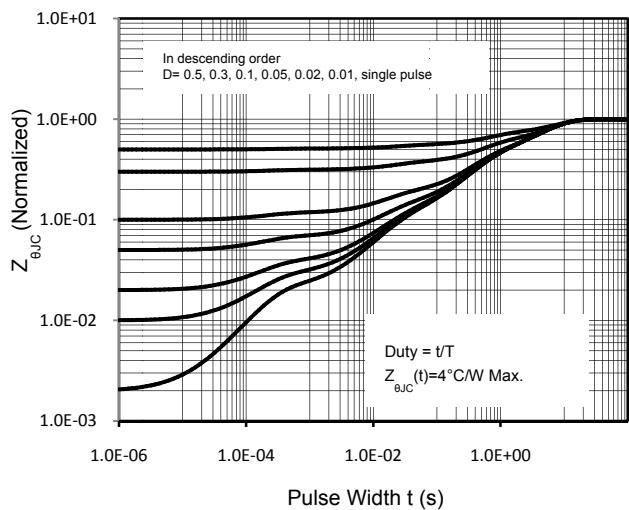


Figure 13. Transient Thermal Response Curve (TO-220F)    Figure 14. Transient Thermal Response Curve

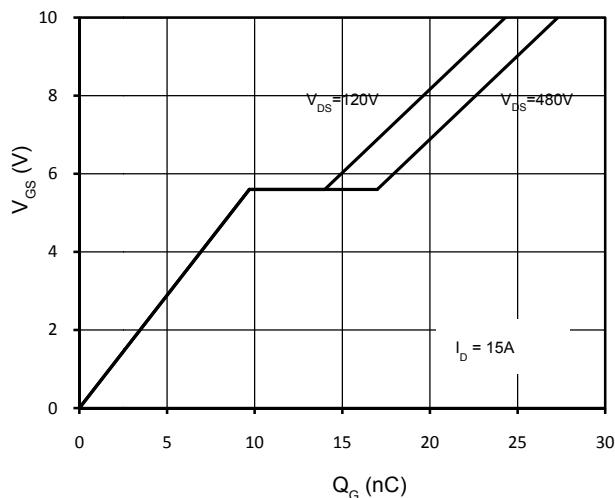
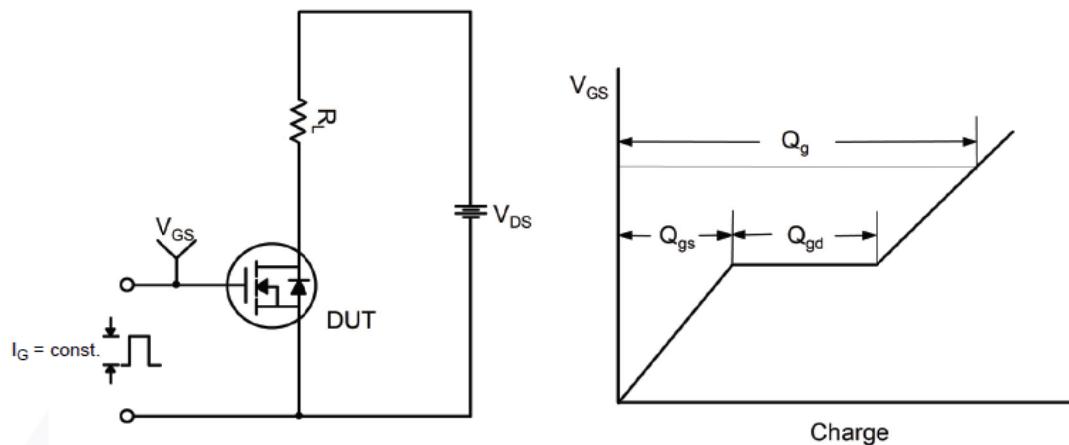
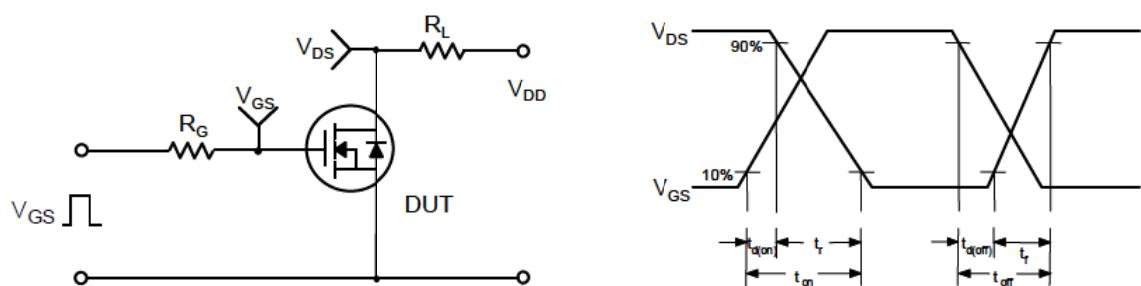
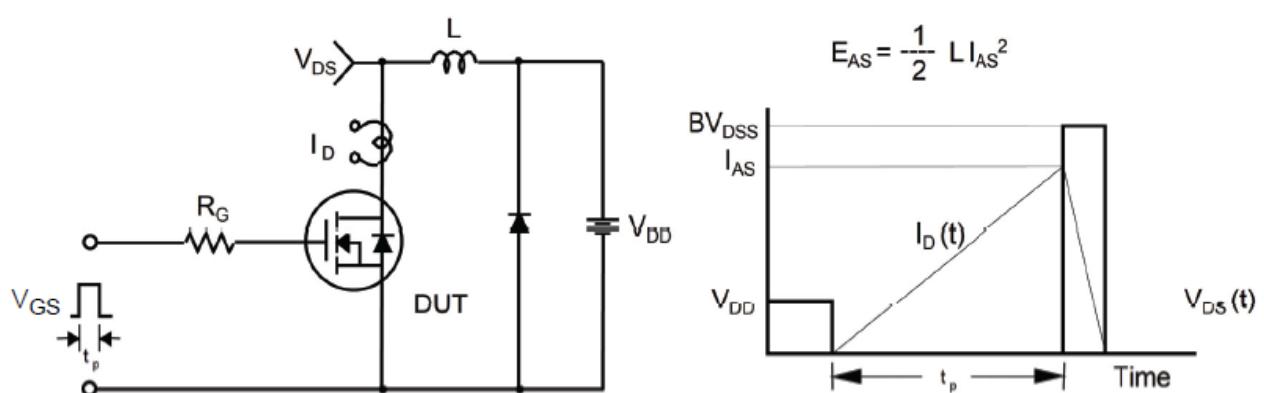
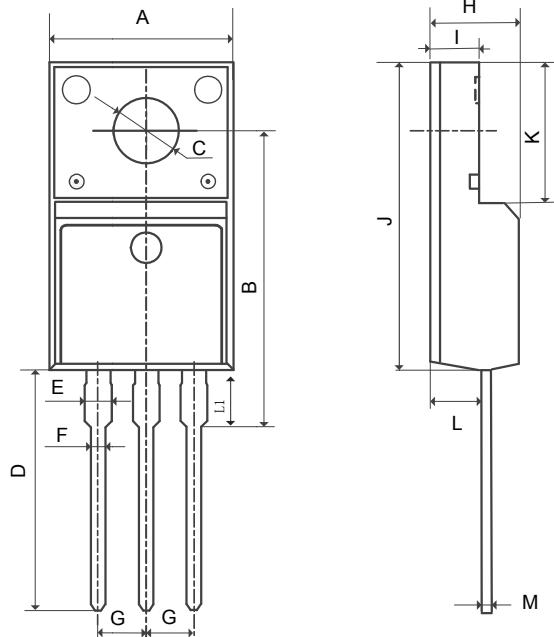
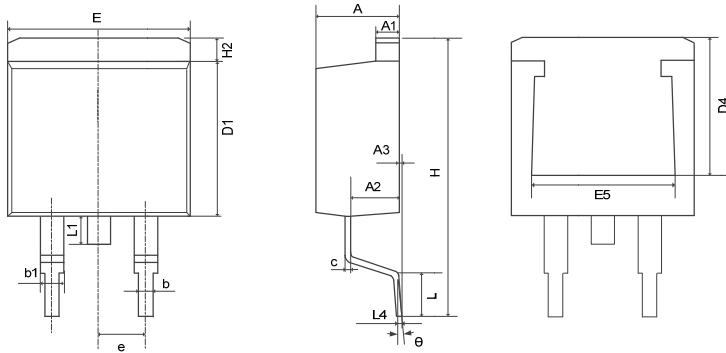


Figure 15. Gate Charge Characteristics

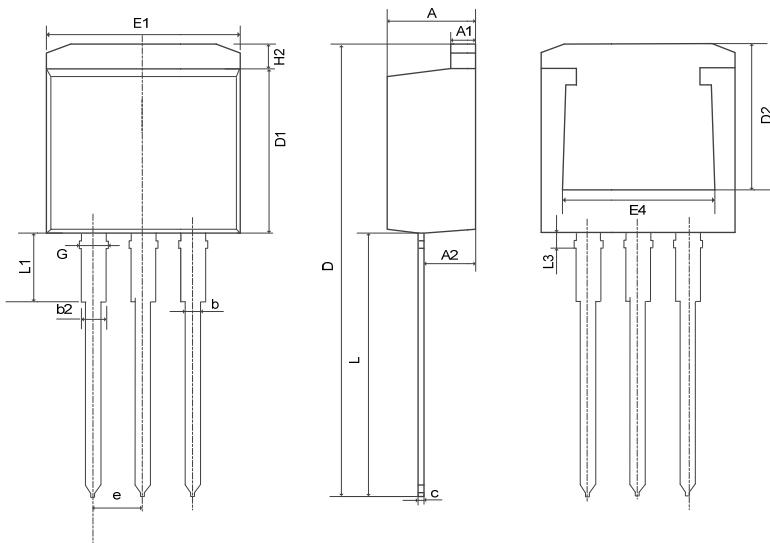
**Gate Charge Test Circuit & Waveform****Switching Test Circuit & Waveforms****Unclamped Inductive Switching Test Circuit & Waveforms**

**Mechanical Dimensions for TO-220F****COMMON DIMENSIONS**

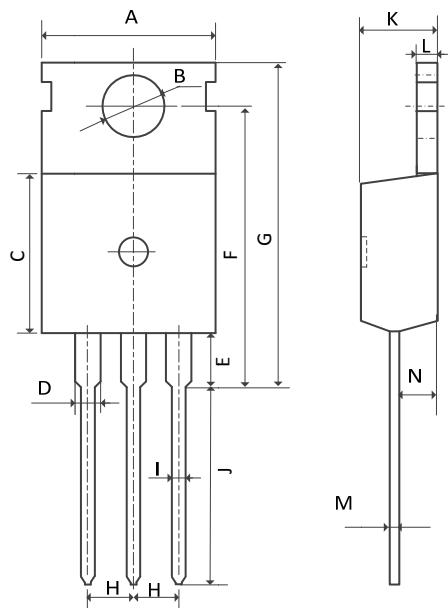
SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

**Mechanical Dimensions for TO-263****COMMON DIMENSIONS**

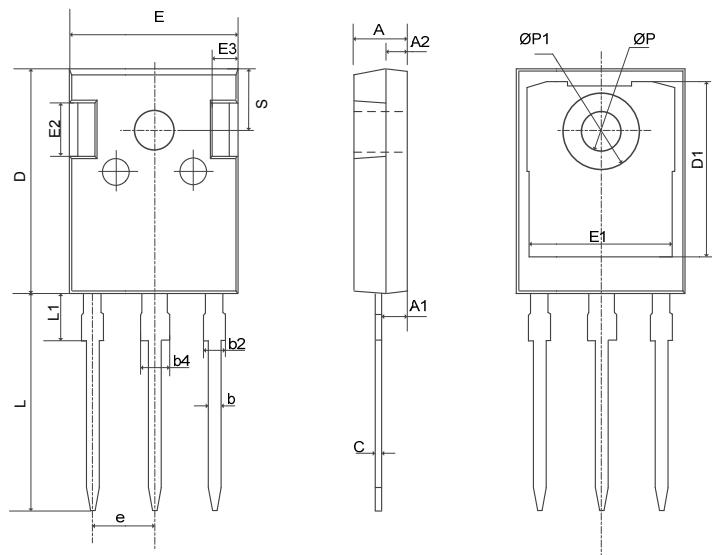
SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.49	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.45	8.90
D4	6.60	—
E	9.86	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.70
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°

**Mechanical Dimensions for TO-262****COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.49	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.53
D	23.20	24.02
D1	8.45	8.90
D2	6.00	—
E1	9.86	10.40
E4	7.06	—
e	2.54BSC	
G	1.25	1.50
H2	—	1.50
L	13.33	14.16
L1	3.50	4.00
L3	1.28	1.58

**Mechanical Dimensions for TO-220****COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

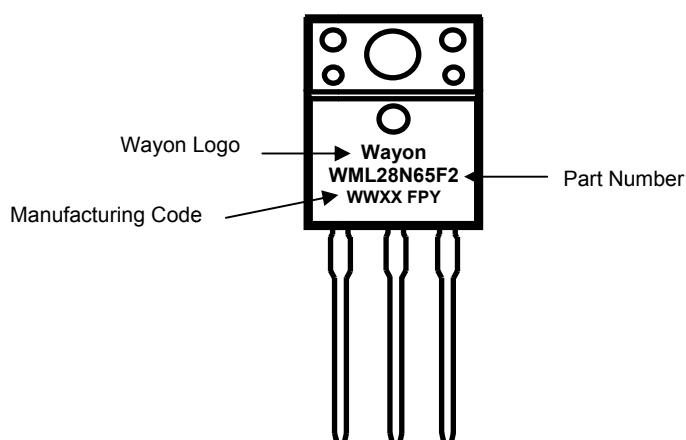
**Mechanical Dimensions for TO-247****COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
b4	2.91	3.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	5.44BSC	
L	19.62	20.22
L1	—	4.30
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

## Ordering Information

Part	Package	Marking	Packing method
WML28N65F2	TO-220F	WML28N65F2	Tube
WMK28N65F2	TO-220	WMK28N65F2	Tube
WMN28N65F2	TO-262	WMN28N65F2	Tube
WMM28N65F2	TO-263	WMM28N65F2	Tape and Reel
WMJ28N65F2	TO-247	WMJ28N65F2	Tube

## Marking Information



## Contact Information

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